

Taiwan Semiconductor

N-Channel Power MOSFET

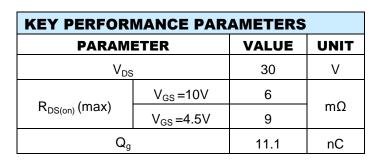
 $30V, 60A, 6m\Omega$

FEATURES

- 100% avalanche tested
- Fast switching
- Pb-free plating
- RoHS compliant
- Halogen-free mold compound

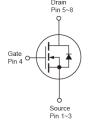
APPLICATION

- Mobile device DC-DC conversion
- Point of Load (POL) DC-DC
- Secondary Switch Rectification









Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current (Note 1)	$T_{\rm C} = 25^{\circ}{\rm C}$		60	•	
	$T_{c} = 100^{\circ}C$	I _D	38	A	
Pulsed Drain Current (Note 2)		I _{DM}	240	А	
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	88	mJ	
Single Pulsed Avalanche Current (Note 3)		I _{AS}	42	А	
Total Power Dissipation @ $T_c = 25^{\circ}C$		P _{DTOT}	45	W	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	$R_{\Theta Jc}$	2.8	°C/W	
Junction to Ambient Thermal Resistance	R _{eja}	62	°C/W	

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air



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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)							
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT	
Static (Note 4)							
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 uA$	V _{GS(TH)}	1.2	1.6	2.5	V	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA	
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I _{DSS}			1	μA	
Ducia Courses On Otata Decistance	V _{GS} = 10V, I _D = 20A			4.8	6		
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 10A$	R _{DS(ON)}		6.7	9	mΩ	
Dynamic ^(Note 5)							
Total Gate Charge		Qg		11.1			
Gate-Source Charge	$V_{DS} = 15V, I_D = 20A,$	Q _{gs}		1.85		nC	
Gate-Drain Charge	$-V_{GS} = 4.5V$	Q _{gd}		6.8			
Input Capacitance		C _{iss}		1210			
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		190		pF	
Reverse Transfer Capacitance		C _{rss}		100			
Switching (Note 6)							
Turn-On Delay Time		t _{d(on)}		7.5			
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 15V,$	t _r		14.5			
Turn-Off Delay Time	$R_{G} = 3.3\Omega, I_{D} = 15A$	t _{d(off)}		35.2		ns	
Turn-Off Fall Time		t _f		9.6			
Source-Drain Diode ^(Note 4)	·						
Diode Forward Voltage	V _{GS} =0V, I _S =1A	V _{SD}			1	V	

Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

3. L = 0.1mH, I_{AS} = 42A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}$ C

4. Pulse test: PW \leq 300µs, duty cycle \leq 2%

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.



ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM060N03PQ33 RGG	PDFN33	5,000pcs / 13"Reel

Note:

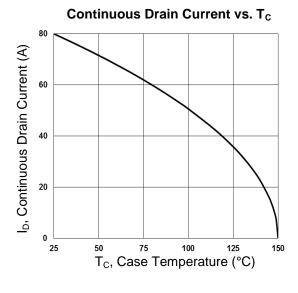
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

2. Halogen-free according to IEC 61249-2-21 definition

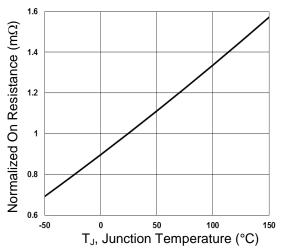


CHARACTERISTICS CURVES

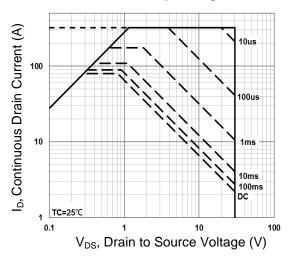
(T_C = 25°C unless otherwise noted)

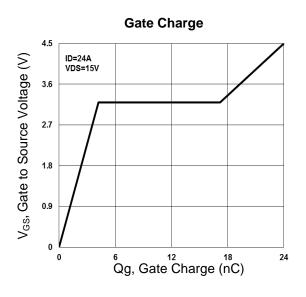


On-Resistance vs. Junction Temperature

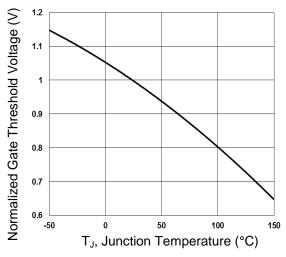


Maximum Safe Operating Area

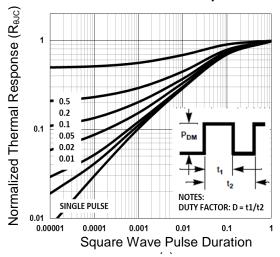




Threshold Voltage vs. Junction Temperature

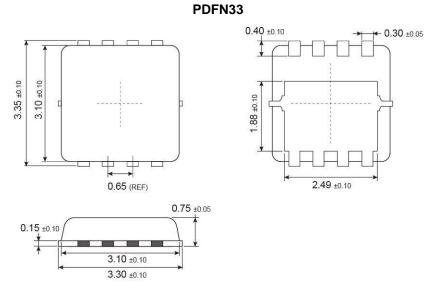


Normalized Thermal Transient Impedance Curve

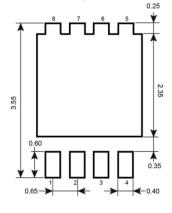




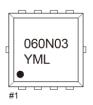
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y	= Y	′ear	Cod	de

•							
Μ	= Month Code for Halogen Free Product						
	O =Jan	Ρ	=Feb	Q	=Mar	R	=Apr
•	S =May	т	=Jun	U	=Jul	V	=Aug
	W =Sep	Х	=Oct	Υ	=Nov	Ζ	=Dec
L	= Lot Code (1-	-9,	A~Z)				



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